

# 2SB1377

## Silicon PNP epitaxial planer type

For low-frequency power amplification and driver amplification  
Complementary to 2SD2071

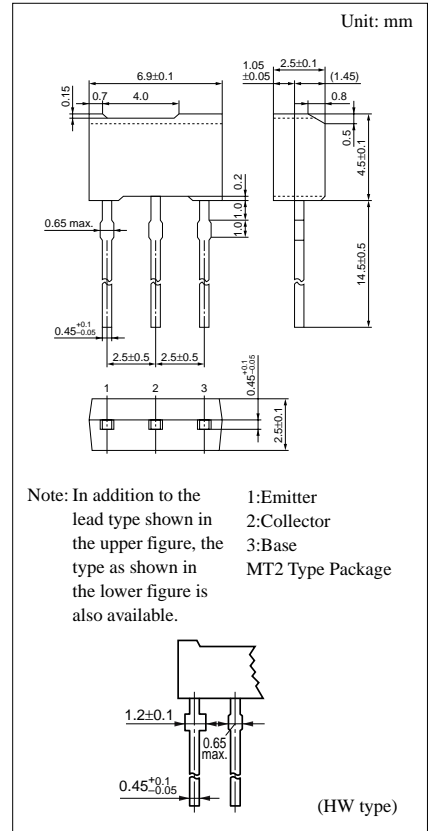
### ■ Features

- Allowing supply with the radial taping.

### ■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-60	V
Collector to emitter voltage	$V_{CEO}$	-50	V
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-1	A
Collector current	$I_C$	-500	mA
Collector power dissipation	$P_C^*$	1	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 ~ +150	°C

\* Printed circuit board: Copper foil area of 1cm<sup>2</sup> or more, and the board thickness of 1.7mm for the collector portion



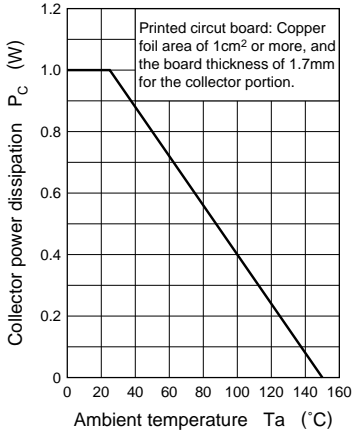
### ■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -20V, I_E = 0$			-0.1	μA
	$I_{CEO}$	$V_{CE} = -20V, I_B = 0$			-1	μA
Collector to base voltage	$V_{CBO}$	$I_C = -10\mu A, I_E = 0$	-60			V
Collector to emitter voltage	$V_{CEO}$	$I_C = -2mA, I_B = 0$	-50			V
Emitter to base voltage	$V_{EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = -10V, I_C = -10mA$	85	160	340	
	$h_{FE2}$	$V_{CE} = -10V, I_C = -500mA$	40	90		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -300mA, I_B = -30mA$		-0.35	-0.6	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -300mA, I_B = -30mA$		-1.1	-1.5	V
Transition frequency	$f_T$	$V_{CB} = -10V, I_E = 10mA, f = 200MHz$		200		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$		6	15	pF

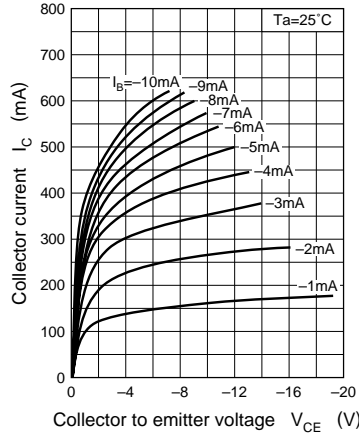
\* $h_{FE1}$  Rank classification

Rank	Q	R	S
$h_{FE1}$	85 ~ 170	120 ~ 240	170 ~ 340

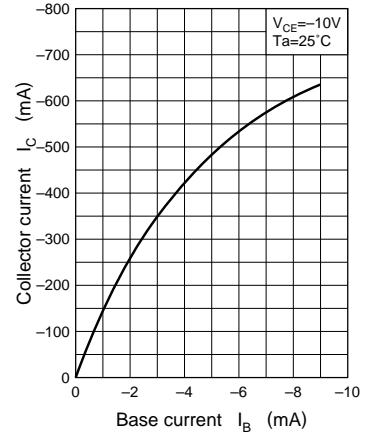
$P_C - T_a$



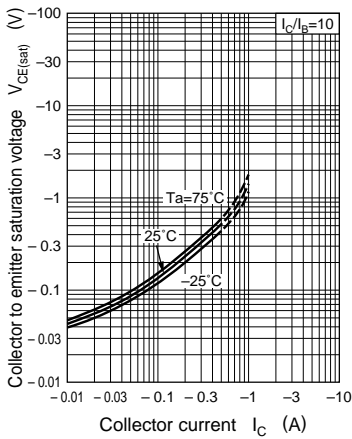
$I_C - V_{CE}$



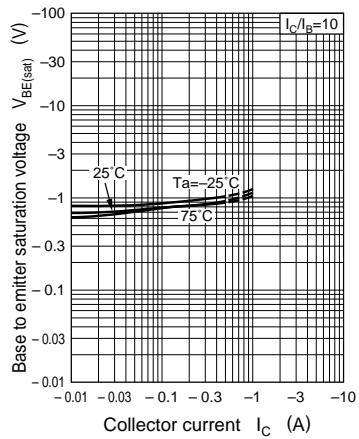
$I_C - I_B$



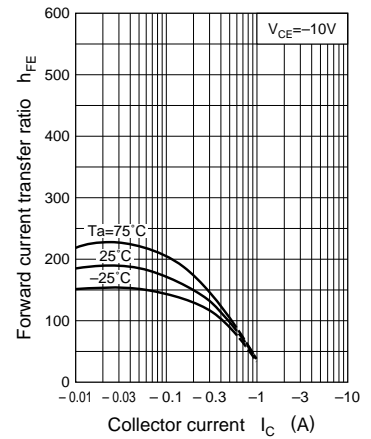
$V_{CE(sat)} - I_C$



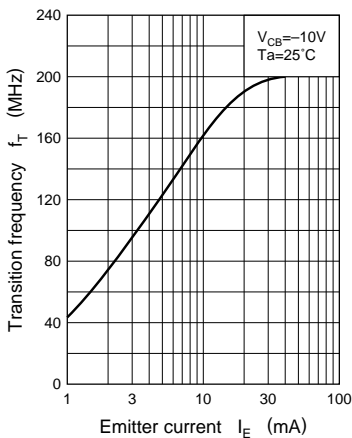
$V_{BE(sat)} - I_C$



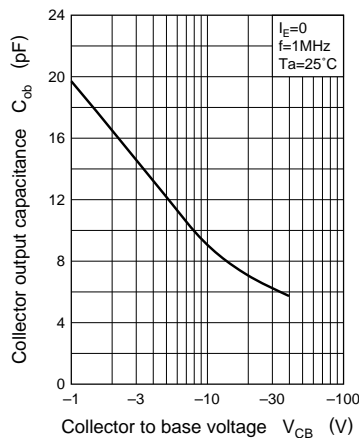
$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$



$V_{CER} - R_{BE}$

